

Driver Transistors

LMBTA05LT1
LMBTA06LT1

FEATURES

- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish

MAXIMUM RATINGS

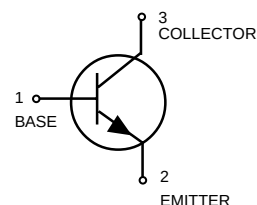
Rating	Symbol	Value		Unit
		LMBTA05	LMBTA06	
Collector-Emitter Voltage	V_{CEO}	60	80	Vdc
Collector-Base Voltage	V_{CBO}	60	80	Vdc
Emitter-Base Voltage	V_{EBO}	4.0		Vdc
Collector Current — Continuous	I_C	500		mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (1) $T_A = 25^\circ\text{C}$	P_D	225	mW
Derate above 25°C		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate, (2) $T_A = 25^\circ\text{C}$	P_D	300	mW
Derate above 25°C		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$



SOT-23



DEVICE MARKING

LMBTA05LT1 = 1H, LMBTA06LT1 = 1GM

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage(3) ($I_C = 1.0 \text{ mAdc}, I_B = 0$)	$V_{(BR)CEO}$			Vdc
LMBTA05		60	—	
LMBTA06		80	—	
Emitter-Base Breakdown Voltage ($I_E = 100 \mu\text{Adc}, I_C = 0$)	$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 60\text{Vdc}, I_B = 0$)	I_{CES}	—	0.1	μAdc
Emitter Cutoff Current ($V_{CB} = 60\text{Vdc}, I_E = 0$)	I_{CBO}	—	0.1	μAdc
($V_{CB} = 80\text{Vdc}, I_E = 0$)		—	0.1	

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.

3. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
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ON CHARACTERISTICS

DC Current Gain ($I_C = 10\text{ mA}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 100\text{ mA}$, $V_{CE} = 1.0\text{ Vdc}$)	h_{FE}	100 100	— —	—
Collector-Emitter Saturation Voltage ($I_C = 100\text{ mA}$, $I_B = 10\text{ mA}$)	$V_{CE(sat)}$	—	0.25	Vdc
Base-Emitter On Voltage ($I_C = 100\text{ mA}$, $V_{CE} = 1.0\text{ Vdc}$)	$V_{BE(sat)}$	—	1.2	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current –Gain – Bandwidth Product(4) ($V_{CE} = 2.0\text{ V}$, $I_C = 10\text{ mA}$, $f = 100\text{ MHz}$)	f_T	100	—	MHz
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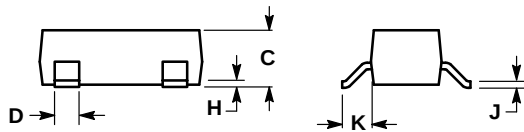
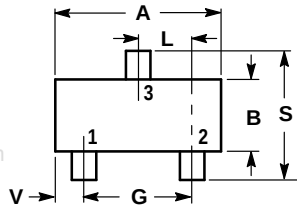
4. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

ORDERING INFORMATION

Device	Package	Shipping
LMBTA05LT1	SOT-23	3000/Tape & Reel
LMBTA05LT1G	SOT-23	3000/Tape & Reel
LMBTA06LT1	SOT-23	3000/Tape & Reel
LMBTA06LT1G	SOT-23	3000/Tape & Reel

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NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

- PIN 1. BASE
2. EMITTER
3. COLLECTOR

